

EFC6605R

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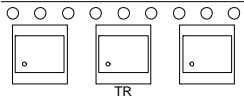
Parameter	Symbol	Conditions	Value			Unit
			min	typ	max	
Turn-ON Delay Time	$t_{d(on)}$	$V_{SS}=10V, V_{GS}=4.5V, I_S=3A$ Test Circuit 6		154		ns
Rise Time	t_r			678		ns
Turn-OFF Delay Time	$t_{d(off)}$			44400		ns
Fall Time	t_f			60800		ns
Total Gate Charge	Q_g	$V_{SS}=10V, V_{GS}=4.5V, I_S=10A$ Test Circuit 7		19.8		nC
Forward Source to Source Voltage	$V_{F(S-S)}$	$I_S=3A, V_{GS}=0V$ Test Circuit 8		0.75	1.2	V

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

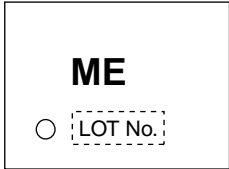
Ordering & Package Information

Device	Package	Shipping	note
EFC6605R-TR	EFCP	5,000 pcs. / reel	Pb-Free and Halogen Free

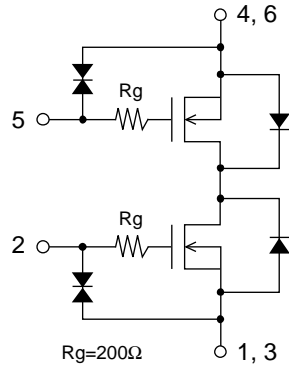
Packing Type: TR



Marking

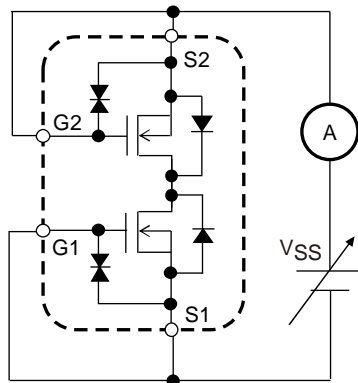


Electrical Connection

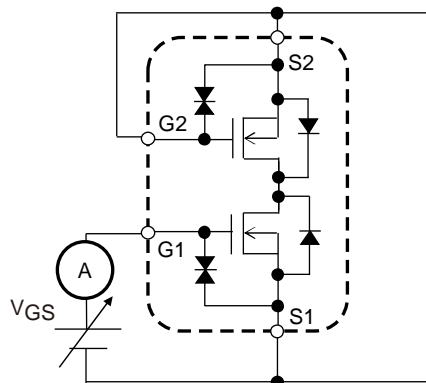


Test circuits are example of measuring FET1 side

Test Circuit 1
 I_{SSS}

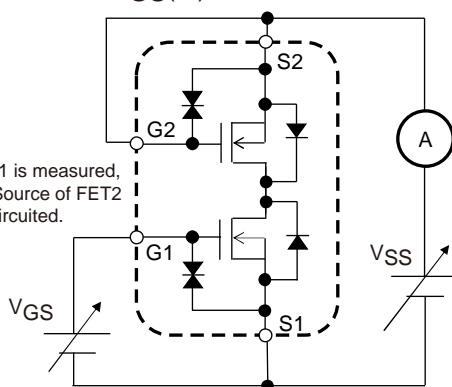


Test Circuit 2
 I_{GSS}



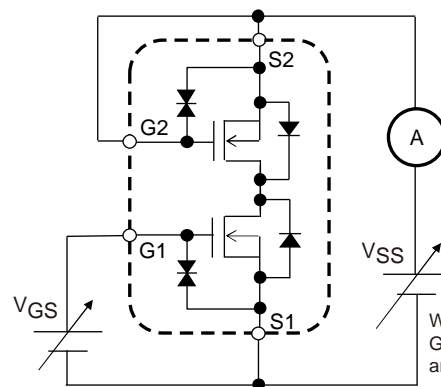
When FET1 is measured, Gate and Source of FET2 are short-circuited.

Test Circuit 3
 $V_{GS(th)}$



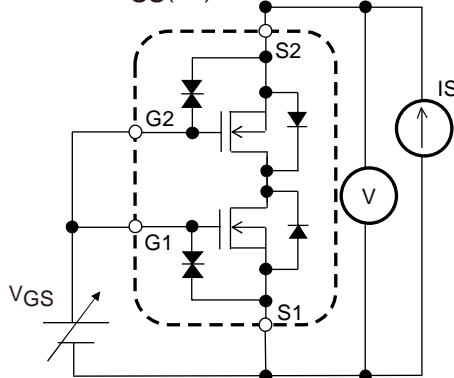
When FET1 is measured, Gate and Source of FET2 are short-circuited.

Test Circuit 4
 g_{FS}

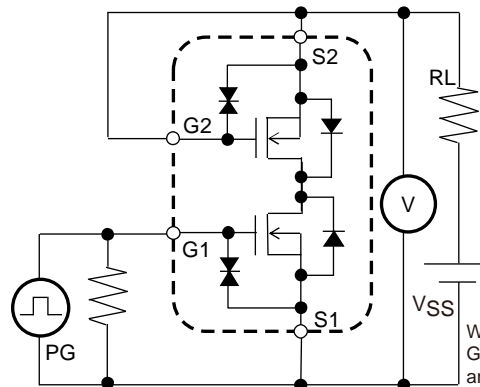


When FET1 is measured, Gate and Source of FET2 are short-circuited.

Test Circuit 5
 $R_{SS(on)}$

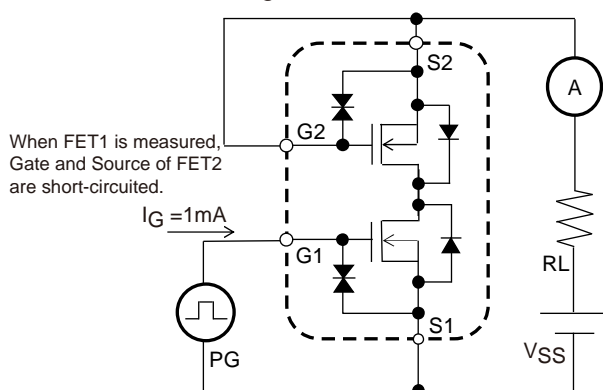


Test Circuit 6
 $t_{d(on)}$, t_r , $t_{d(off)}$, t_f



When FET1 is measured, Gate and Source of FET2 are short-circuited.

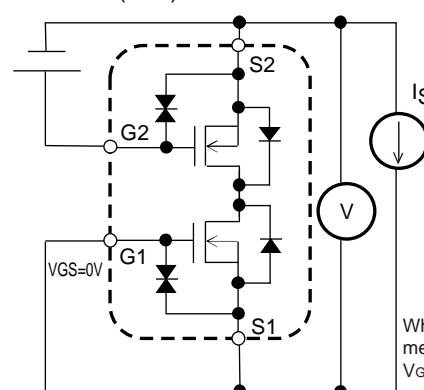
Test Circuit 7
 Q_g



When FET1 is measured, Gate and Source of FET2 are short-circuited.

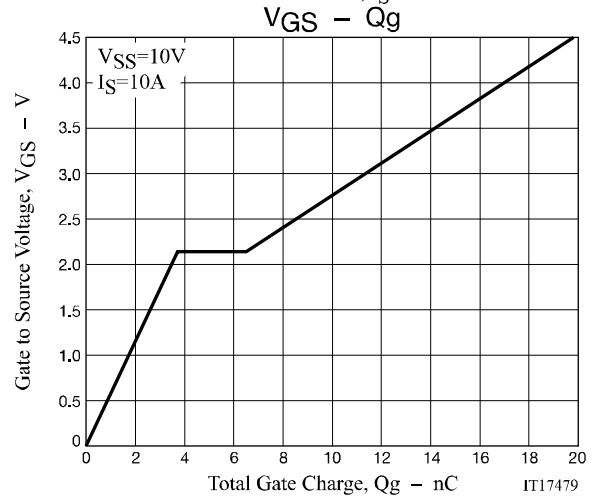
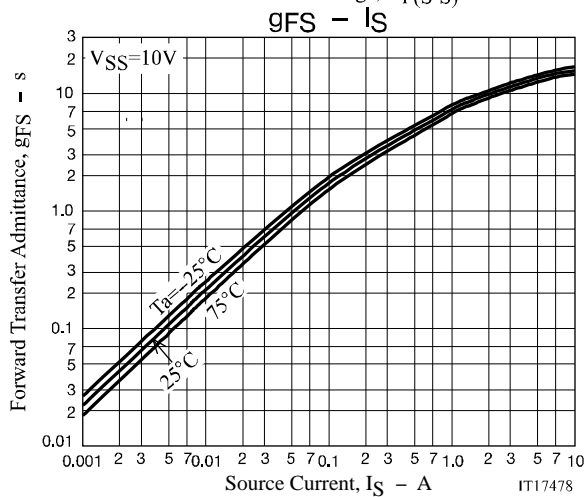
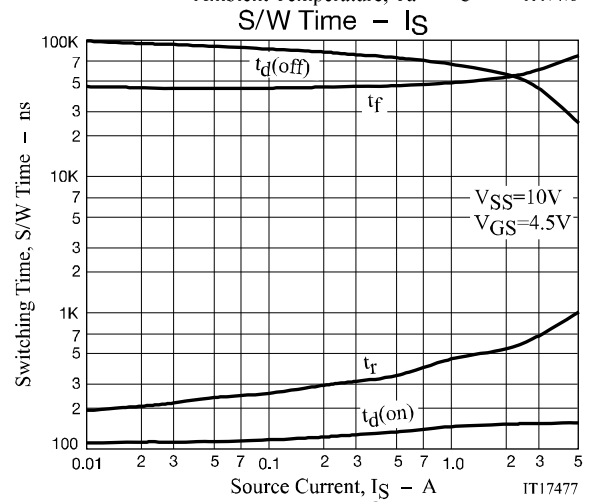
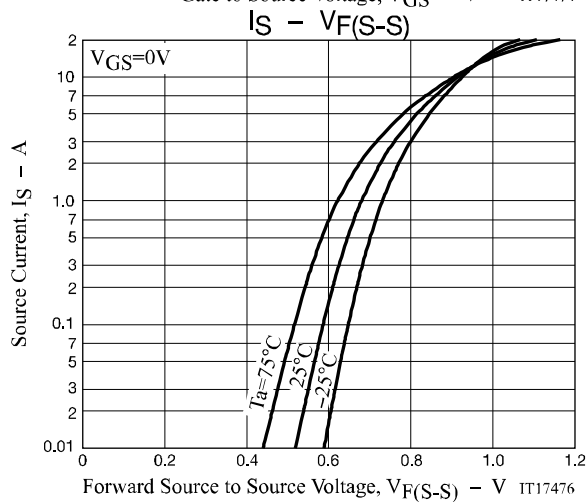
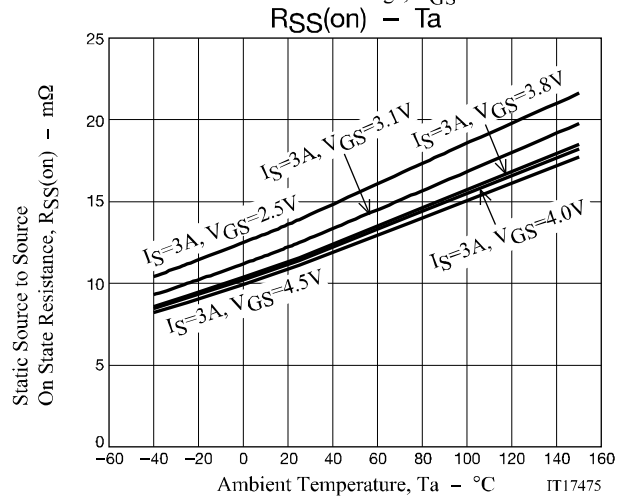
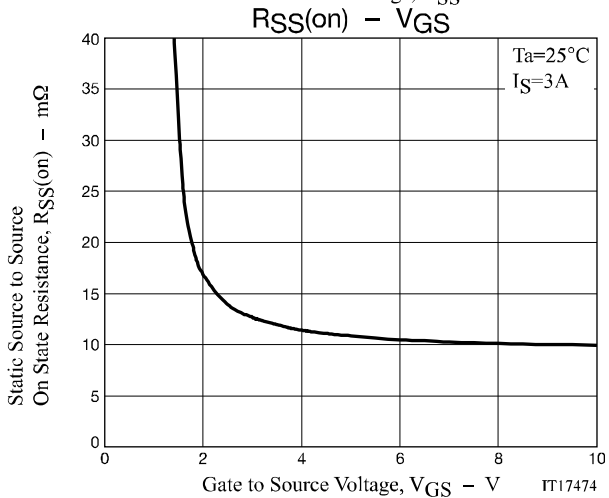
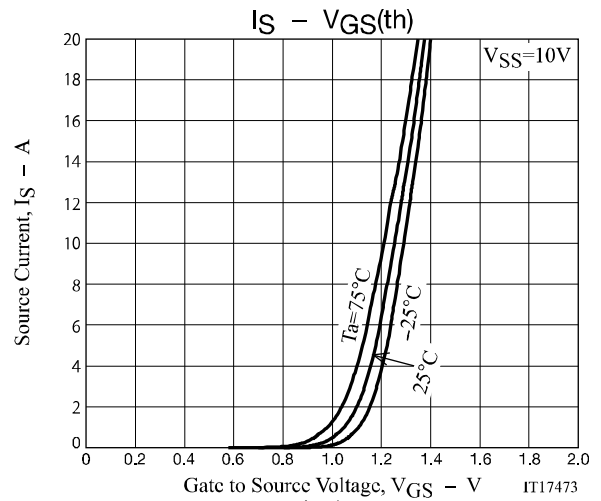
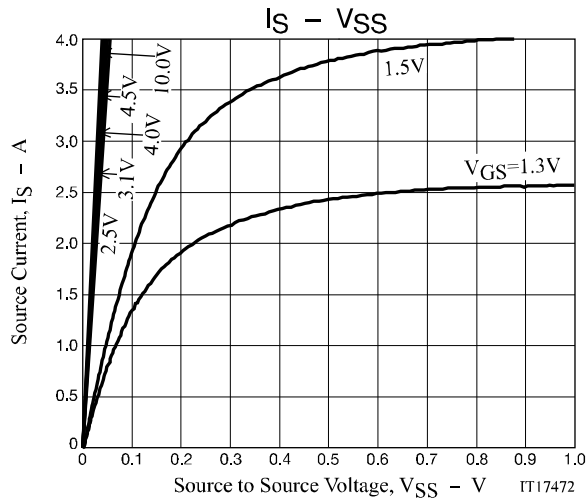
$I_G = 1mA$

Test Circuit 8
 $V_F(S-S)$



When FET1 is measured, +4.5V is added to V_{GS} of FET2.

When FET2 is measured, the position of FET1 and FET2 is switched.



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